CLAIMS

What is claimed is :

1. A conductive structure, comprising:

stair step structures positioned along a length of the conductive structure, each stair step structure comprising at least two conductive steps, each conductive step of the at least two conductive steps being at least partially separated from an adjacent conductive step of the at least two conductive steps by insulative material;

at least one landing comprising at least one via extending through the conductive structure underlying and defining the at least one landing, the at least one landing positioned between a first stair step structure of the stair step structures and a second stair step structure of the stair step structures positioned adjacent to the first stair step structure; and

access lines, each access line in communication with a conductive portion of one conductive step of the at least two conductive steps of the stair step structures and extending from the one conductive step to, and being in communication with, the at least one via extending through the conductive structure underlying and defining the at least one landing.

2. The conductive structure of claim 1, wherein the at least one via comprises a plurality of vias, and wherein each access line extends from a conductive portion of one conductive step of at least two conductive steps of the stair step structures to one via of the plurality of vias.

3. The conductive structure of claim 1, further comprising at least one pair of additional stair step structures and at least one additional landing, each additional stair step structure of the at least one pair of additional stair step structures opposing another stair step structure of the at least one pair with the at least one additional landing therebetween.

4. The conductive structure of claim 1, wherein at least one of the stair step structures lacks access lines connected to conductive steps of the at least one stair step structure.

5. The conductive structure of claim 1, wherein the at least one landing comprises a plurality of landings, each landing of the plurality of landings being positioned between a pair of the stair step structures.

6. The conductive structure of claim 1, wherein the at least one landing is defined by a stack of alternating first material and second material, wherein the first material and the second material each comprise an insulative material.

7. The conductive structure of claim 1, wherein the at least one landing is defined by a stack of alternating first material and second material, wherein the first material comprises a conductive material and the second material comprises an insulative material.

8. The conductive structure of claim 7, further comprising an insulative liner at least partially surrounding the at least one via and insulating the at least one via from the conductive material of the at least one landing.

9. The conductive structure of claim 1, wherein the at least one via is operably coupled to at least one control unit underlying the stair step structures and the at least one landing.

10. The conductive structure of claim 1, wherein at least some of the stair step structures each comprise a word line plate structure.

11. The conductive structure of claim 1, wherein one stair step structure of the stair step structures comprises a drain select gate (SGD) structure.

12. The conductive structure of claim 1, further comprising stack slot elements extending along a length of the conductive structure.

13. The conductive structure of claim 12, wherein the stack slot elements comprise:

outer stack slot elements extending continuously along a majority of the length of the conductive structure; and

inner stack slot elements extending discontinuously along the length of the conductive structure.

14. The conductive structure of claim 13, wherein the inner stack slot elements are positioned proximate the stair step structures.

15. The conductive structure of claim 14, wherein the at least one landing lacks the inner stack slot elements.

16. The conductive structure of claim 13, wherein the stack slot elements comprise an insulative material positioned over a conductive material deposited in a replacement gate process.

17. A conductive structure, comprising:

tiered structures positioned along a length of the conductive structure, each tiered structure comprising at least two tiers having a conductive portion, each conductive portion of the at least two tiers being at least partially separated from an adjacent conductive portion of the at least two tiers by insulative material; and

a landing comprising vias extending through the conductive structure at the landing, the landing and the vias positioned between a first tiered structure of the tiered structures and a second tiered structure of the tiered structures positioned adjacent to the first tiered structure.

18. The conductive structure of claim 17, further comprising access lines coupling conductive portions of the at least two tiers of the tiered structures to a respective via of the vias.

19. The conductive structure of claim 17, further comprising stack slot elements extending along the length of the conductive structure, wherein at least one stack slot element of the stack slot elements extends discontinuously along the length of the conductive structure.

20. The conductive structure of claim 19, wherein the at least one discontinuous stack slot element at least partially physically and electrically separates at least one tiered structure of the tiered structures into a first sub-tier portion and a second sub-tier portion.

21. The conductive structure of claim 20, wherein a short in the at least one tier defined along an end of the at least one discontinuous stack slot element electrically connects the first sub-tier portion and the second sub-tier portion.

22. The conductive structure of claim 19, wherein the at least one discontinuous stack slot element is positioned laterally within one tiered structure of the tiered structures separated from lateral sides of the conductive structure.

23. The conductive structure of claim 22, wherein at least another stack slot element of the stack slot elements extends continuously along the length of the conductive structure, wherein the at least one continuous stack slot element defines at least a portion of a lateral side of the conductive structure.

24. A device, comprising:

an array of memory cells; and

a conductive structure positioned adjacent to the array of memory cells, the conductive structure comprising:

stair step structures positioned along a length of the conductive structure, each stair step structure being in electrical communication with memory cells of the array;

at least one control device for selecting memory cells of the array;

at least one landing positioned between a first stair step structure of the stair step structures and a second stair step structure of the stair step structures;

vias extending through the at least one landing to the at least one control device; and

access lines coupled between conductive portions of the stair step structures and extending to the at least one landing, each access line of the access lines being

coupled to a first end of a respective via of the vias, wherein a second end of each of the vias is electrically coupled to the at least one control device.

25. The device of claim 24, wherein the stair step structures comprise word line plates.

26. The device of claim 24, wherein each word line plate of the word line plates comprises a contact portion laterally offset from a contact portion of an adjacent word line plate of the word line plates, and wherein each access line of the access lines is in communication with a respective one of the word line plates and couples the respective one of the word line plates to a respective via of the vias.

27. A system, comprising:

at least one electronic signal processor;

a semiconductor device configured to communicate electrically with the at least one electronic signal processor; and

a conductive structure comprising:

stair step structures positioned along a length of the conductive structure, each stair step structure being in electrical communication with the semiconductor device;

at least one landing positioned between a first stair step structure of the stair step structures and a second stair step structure of the stair step structures, the at least one landing comprising:

alternating first materials and second materials, wherein the first materials and the second materials comprise an insulative material; and

vias extending through the first materials and the second materials.

28. The system of claim 27, further comprising at least one stack slot element laterally spaced from an outer lateral boundary of the conductive structure, the at least one stack slot element extending only along the length of the conductive structure proximate the stair step structures.

29. The system of claim 28, wherein the stack slot elements comprise an insulative material and a conductive material, the conductive material defining a conductive portion of one step of the stair step structures.

30. The system of claim 29, further comprising access lines, each access line coupling the conductive portion of the one step of the stair step structures to a respective via of the vias.

31. A method of forming the conductive structure of claim 1, the method comprising:
forming openings through a stack of material at the at least one landing of the conductive structure defined between two of the stair step structures, the two stair step structures being positioned on one side of and in electrical communication with a semiconductor device;
forming contacts in the openings in the stack of the material; and
electrically coupling a conductive portion of at least one step of the stair step structure with at least one contact of the contacts.

32. The method of claim 31, further comprising forming the stack of material with alternating insulative and conductive materials.

33. The method of claim 32, further comprising forming a liner in each opening of the openings to surround a contact therein.

34. The method of claim 31, further comprising forming the stack of material with alternating insulative materials comprising a first insulative material and a second sacrificial insulative material.

35. The method of claim 34, further comprising:
forming an opening through the stack of material;

removing a portion of the second sacrificial insulative material adjacent the opening in a volume of the second sacrificial material underlying the first insulative material; and

depositing a conductive material in the opening and in the volume from which the portion of the second sacrificial material is removed to form the conductive portion of at least one step of the stair step structure.

36. The method of claim 35, further comprising:

removing a portion of the conductive material within the opening; and

depositing another insulative material within the opening.

37. The method of claim 36, further comprising forming an electrical connection between the conductive portion of at least one step of the stair step structure and another, adjacent conductive portion of the at least one step around the another insulative material.

38. The method of claim 31, further comprising performing a replacement gate process on at least one stair step structure of the stair step structures while masking the landing of the conductive structure.